



MMBT4401

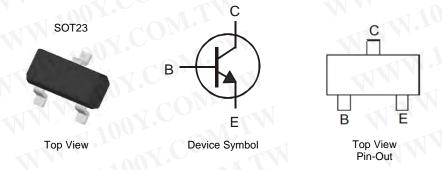
40V NPN SURFACE MOUNT SMALL SIGNAL TRANSISTOR IN SOT23

Features

- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (MMBT4403)
- Ideal for Medium Power Amplification and Switching
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- UL Flammability Rating 94V-0
- Case material: molded Plastic "Green" Compound
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.008 grams (Approximate)



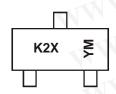
Ordering Information (Note 3 & 4)

					W '
Product	Grade	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT4401-7-F	Commercial	K2X	7 7	8	3,000
MMBT4401-13-F	Commercial	K2X	13	8	10,000
MMBT4401Q-13-F	Automotive	K2X	13	8	10,000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com
 3. For more packaging details, go to our website at http://www.diodes.com.
- 4. Products with Q-suffix are automotive grade. Automotive products are electrical and thermal the same as the commercial, except where specified.

Marking Information



K2X = Product Type Marking Code YM = Date Code Marking

Y = Year (ex: Y = 2011)

M = Month (ex: 9 = September)

ite Code Key												
Year	2010	20	11	2012	2	2013	2014	- 2	2015	2016		2017
Code	X	10 -	Y	Z		Α	В		С	D		E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	10	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 5)	Ic	600	mA

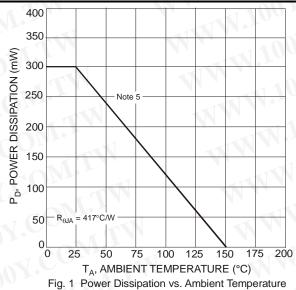
Thermal Characteristics @TA = 25°C unless otherwise specified

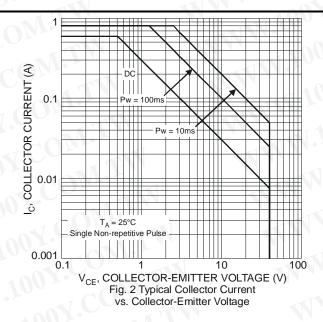
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P _D	300	mW
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	417	°C/W
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	350	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

Notes:

- 5. For a device surface mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Thermal resistance from junction to solder-point (at the end of the collector lead).

Typical Thermal Characteristics







勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-34970699 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw

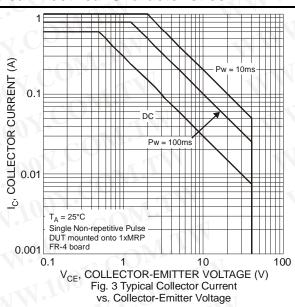
MMBT4401

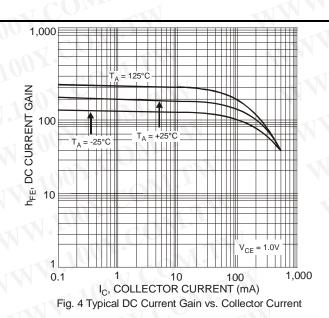
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			44	- 1	1110
Collector-Base Breakdown Voltage	BV _{CBO}	60		V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	40	-11	V	$I_C = 1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0	_ `	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}	x1 —	100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$
Base Cutoff Current	I _{BL}		100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$
ON CHARACTERISTICS (Note 7)		-		-41	M. T. C() 1/2
DC Current Gain	h _{FE}	20 40 80 100 40			$I_{C} = 100\mu A, V_{CE} = 1.0V$ $I_{C} = 1.0mA, V_{CE} = 1.0V$ $I_{C} = 10mA, V_{CE} = 1.0V$ $I_{C} = 150mA, V_{CE} = 1.0V$ $I_{C} = 500mA, V_{CE} = 2.0V$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	FVI	0.40 0.75	V	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$ $I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.75 —	0.95 1.2	V	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$ $I_C = 500 \text{mA}, I_B = 50 \text{mA}$
SMALL SIGNAL CHARACTERISTICS	MV 3				100
Output Capacitance	C _{cb}	ME	6.5	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C_eb	- 1	30	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_C = 0$
Input Impedance	h _{ie}	1.0	15	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h _{fe}	40	500	_	f = 1.0kHz
Output Admittance	h _{oe}	1.0	30	μS	-111
Current Gain-Bandwidth Product	fT	250	T	MHz	$V_{CE} = 10V, I_{C} = 20mA,$ f = 100MHz
SWITCHING CHARACTERISTICS	110	CAL			
Delay Time	t _d		15	ns	$V_{CC} = 30V, I_C = 150mA,$
Rise Time	t_{r}	50	20	ns	$V_{BE(off)} = 2.0V, I_{B1} = 15mA$
Storage Time	t _s		225	ns	$V_{CC} = 30V, I_C = 150mA,$
Fall Time	t _f		30	ns	$I_{B1} = I_{B2} = 15mA$

Notes: 7. Short duration pulse test used to minimize self-heating effect.

Typical Electrical Characteristics







Typical Electrical Characteristics – Continued

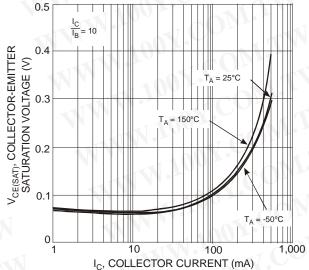
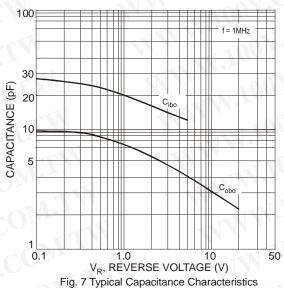


Fig. 5 Collector-Emitter Saturation Voltage vs. Collector Current



2.0 VOLTAGE (V) 1.8 = 1mA 1.6 I_C = 100mA I_C = 300mA COLLECTOR-EMITTER 1.2 1.0 0.8 0.6 0.4 0.2 0.001 100 0.01 0.1 I_B, BASE CURRENT (mA) Fig. 9 Typical Collector Saturation Region

V_{BE(ON)}, BASE-EMITTER TURN-ON VOLTAGE (V) $V_{CE} = 5V$ 0.9 T_A = -50°C 0.8 0.7 T_A = 25°C 0.6 T_A = 150°C 0.4 0.3 0.2 0.1 10 100 I_C, COLLECTOR CURRENT (mA)

Fig. 6 Typical Base-Emitter Turn-On Voltage vs. Collector Current

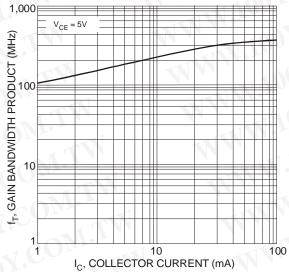
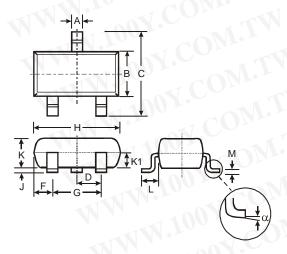


Fig. 8 Typical Gain Bandwidth Product vs. Collector Current

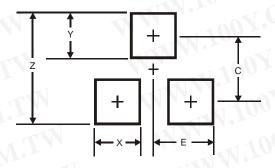


Package Outline Dimensions



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
₋ M	0.085	0.18	0.11				
α	0°	8°	-				
All	All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
C	2.0
E	1.35



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